



BUK9515-100A

N-channel TrenchMOS logic level FET

Rev. 3 — 19 April 2011

Product data sheet

1. Product profile

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance

1.3 Applications

- Automotive and general purpose power switching

1.4 Quick reference data

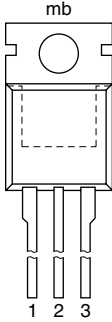
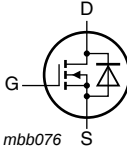
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	T _{mb} = 25 °C	-	-	75	A
P _{tot}	total power dissipation		-	-	230	W
T _j	junction temperature		-55	-	175	°C
Static characteristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	11.5	14.4	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C	-	12	15	mΩ
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I _D = 35 A; V _{sup} ≤ 25 V; R _{GS} = 50 Ω; V _{GS} = 5 V; T _{j(init)} = 25 °C; unclamped	-	-	120	mJ



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

SOT78A (TO-220AB)

3. Ordering information

Table 3. Ordering information

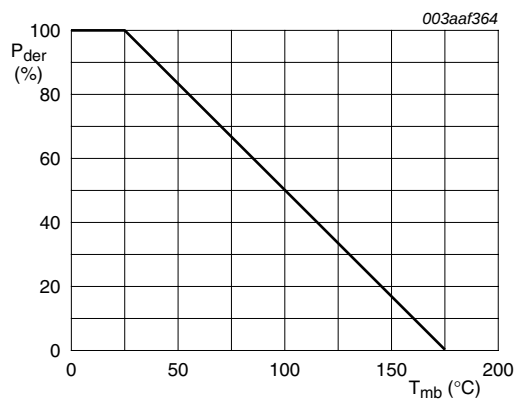
Type number	Package		
	Name	Description	Version
BUK9515-100A	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78A

4. Limiting values

Table 4. Limiting values

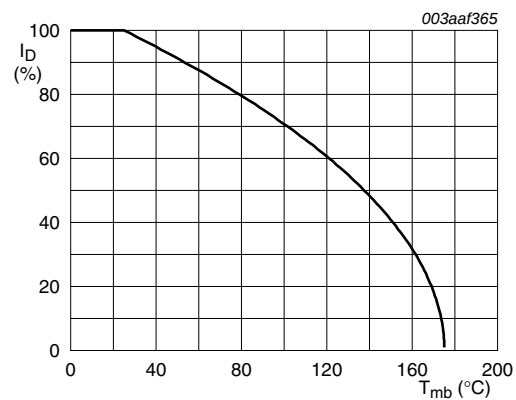
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ }^{\circ}\text{C}$; $T_j \leq 175\text{ }^{\circ}\text{C}$	-	100	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	100	V
V_{GS}	gate-source voltage		-10	10	V
I_D	drain current	$T_{mb} = 25\text{ }^{\circ}\text{C}$	-	75	A
		$T_{mb} = 100\text{ }^{\circ}\text{C}$	-	53	A
I_{DM}	peak drain current	$T_{mb} = 25\text{ }^{\circ}\text{C}$; pulsed	-	313	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ }^{\circ}\text{C}$	-	230	W
T_{stg}	storage temperature		-55	175	$^{\circ}\text{C}$
T_j	junction temperature		-55	175	$^{\circ}\text{C}$
V_{GSM}	peak gate-source voltage	pulsed; $t_p \leq 50\text{ }\mu\text{s}$	-15	15	V
Source-drain diode					
I_S	source current	$T_{mb} = 25\text{ }^{\circ}\text{C}$	-	75	A
I_{SM}	peak source current	pulsed; $T_{mb} = 25\text{ }^{\circ}\text{C}$	-	313	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 35\text{ A}$; $V_{sup} \leq 25\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 5\text{ V}$; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$; unclamped	-	120	mJ



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

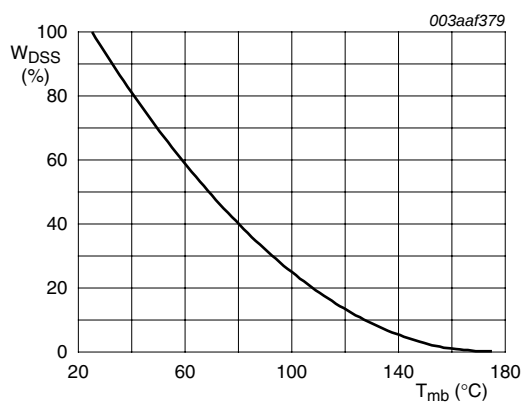
Fig 1. Normalized total power dissipation as a function of mounting base temperature



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

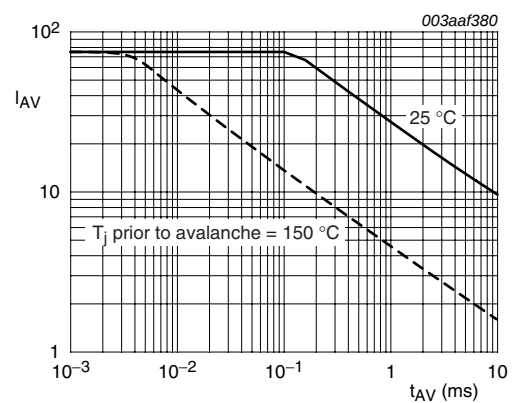
V_{GS} ≥ 5 V

Fig 2. Normalized continuous drain current as a function of mounting base temperature



I_D = 75 A

Fig 3. Normalised drain-source non-repetitive avalanche energy as a function of mounting-base temperature



unclamped inductive load

Fig 4. Single-shot avalanche rating; avalanche current as a function of avalanche period

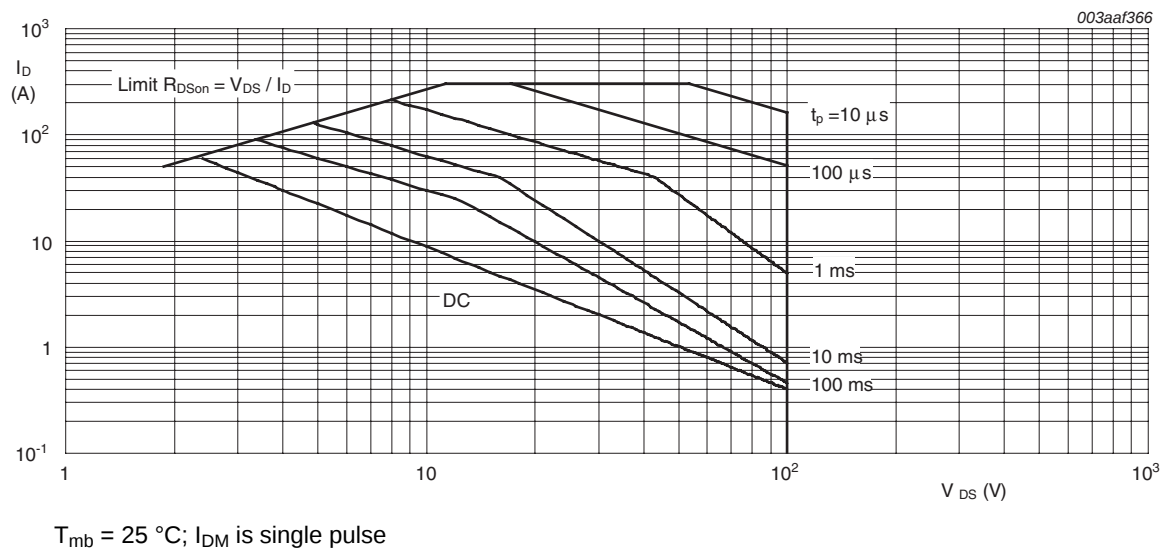


Fig 5. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	0.65	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

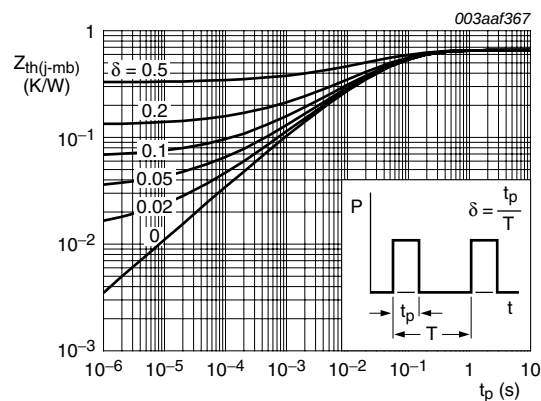


Fig 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 0.25 mA; V _{GS} = 0 V; T _j = 25 °C	100	-	-	V
		I _D = 0.25 mA; V _{GS} = 0 V; T _j = -55 °C	89	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C	1	1.5	2	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C	-	-	2.3	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C	0.5	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	-	0.05	10	μA
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C	-	-	16	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C	-	-	40.5	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	11.5	14.4	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C	-	12	15	mΩ
Dynamic characteristics						
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _j = 25 °C	-	6500	8600	pF
C _{oss}	output capacitance		-	550	660	pF
C _{rss}	reverse transfer capacitance		-	325	400	pF
t _{d(on)}	turn-on delay time	V _{DS} = 30 V; R _L = 1.2 Ω; V _{GS} = 5 V; R _{G(ext)} = 10 Ω; T _j = 25 °C	-	45	65	ns
t _r	rise time		-	130	195	ns
t _{d(off)}	turn-off delay time		-	400	560	ns
t _f	fall time		-	130	190	ns
L _D	internal drain inductance	measured from contact screw on mounting base to centre of die; T _j = 25 °C	-	3.5	-	nH
		measured from drain lead 6 mm from package to centre of die; T _j = 25 °C	-	4.5	-	nH
L _S	internal source inductance	measured from source lead to source bond pad; T _j = 25 °C	-	7.5	-	nH
Source-drain diode						
V _{SD}	source-drain voltage	I _S = 75 A; V _{GS} = 0 V; T _j = 25 °C	-	1.1	-	V
		I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C	-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 75 A; dI _S /dt = -100 A/μs; V _{GS} = -10 V; V _{DS} = 30 V; T _j = 25 °C	-	60	-	ns
Q _r	recovered charge		-	0.24	-	μC

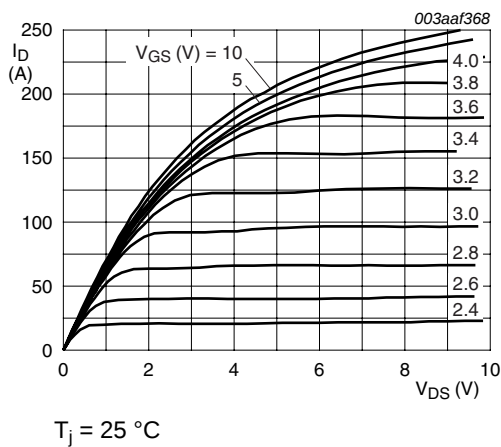


Fig 7. Output characteristics: drain current as a function of drain-source voltage; typical values

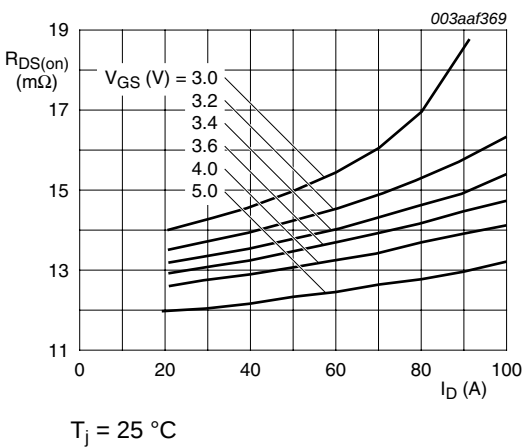


Fig 8. Drain-source on-state resistance as a function of drain current; typical values

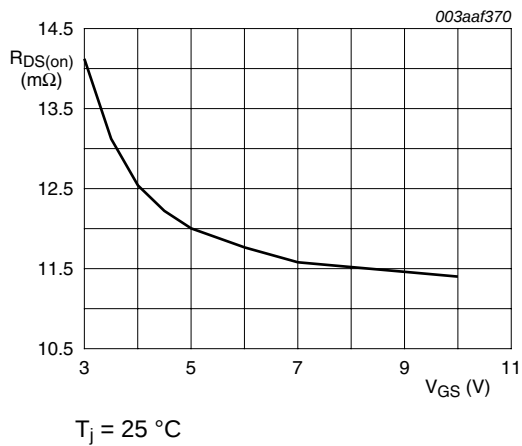


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

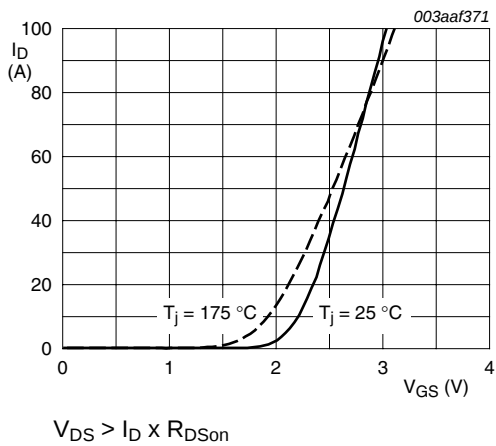


Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

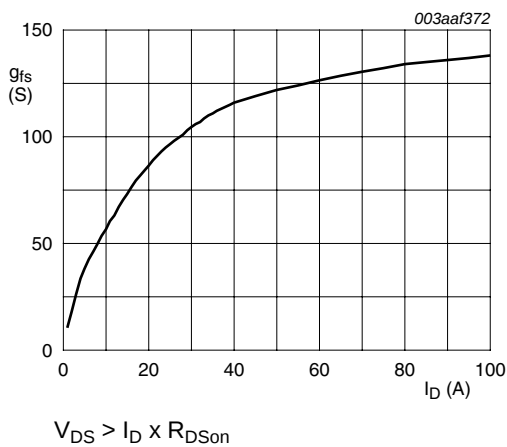


Fig 11. Forward transconductance as a function of drain current; typical values

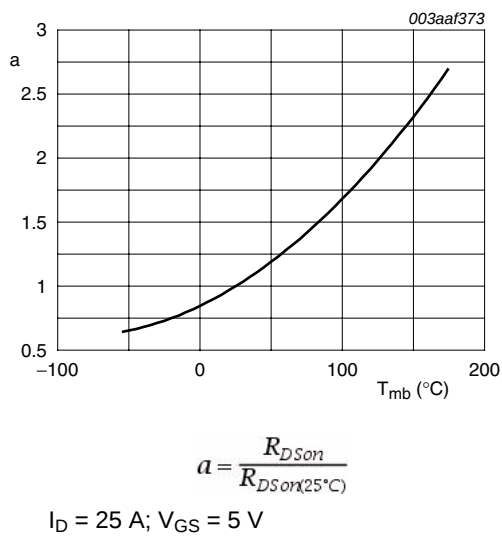


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

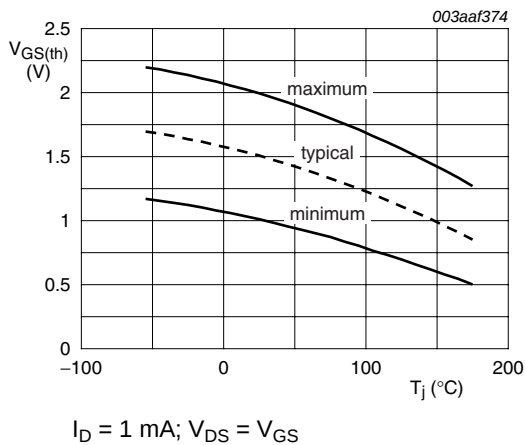


Fig 13. Gate-source threshold voltage as a function of junction temperature

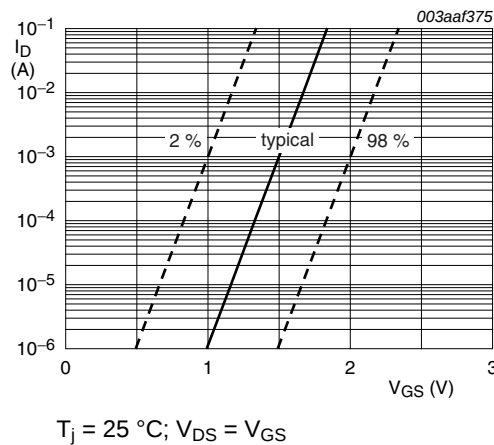


Fig 14. Sub-threshold drain current as a function of gate-source voltage

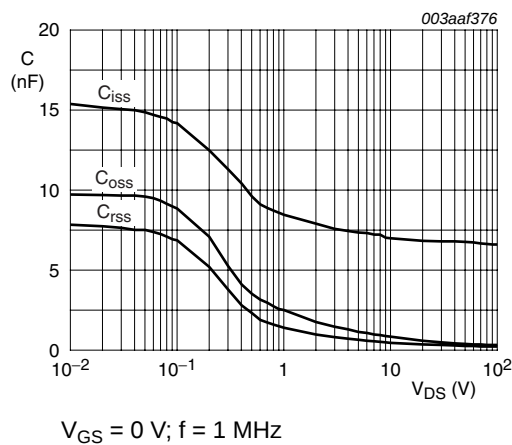


Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

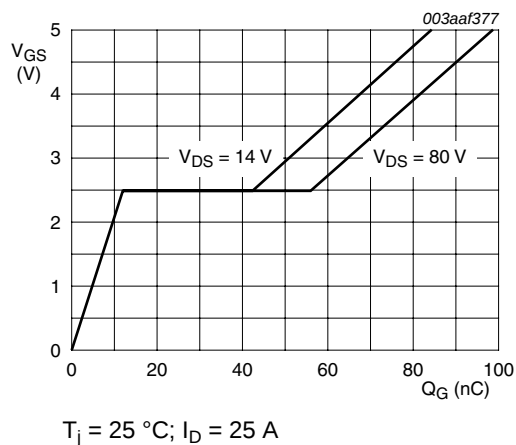


Fig 16. Gate-source voltage as a function of gate charge; typical values

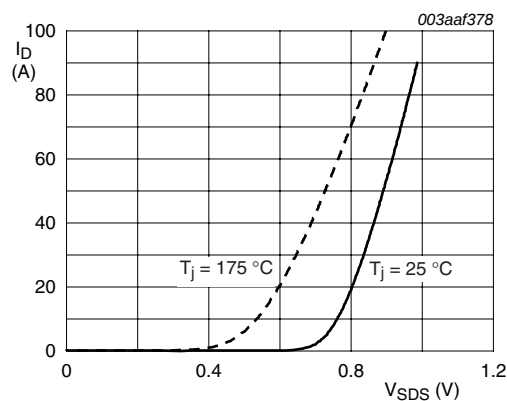


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78A

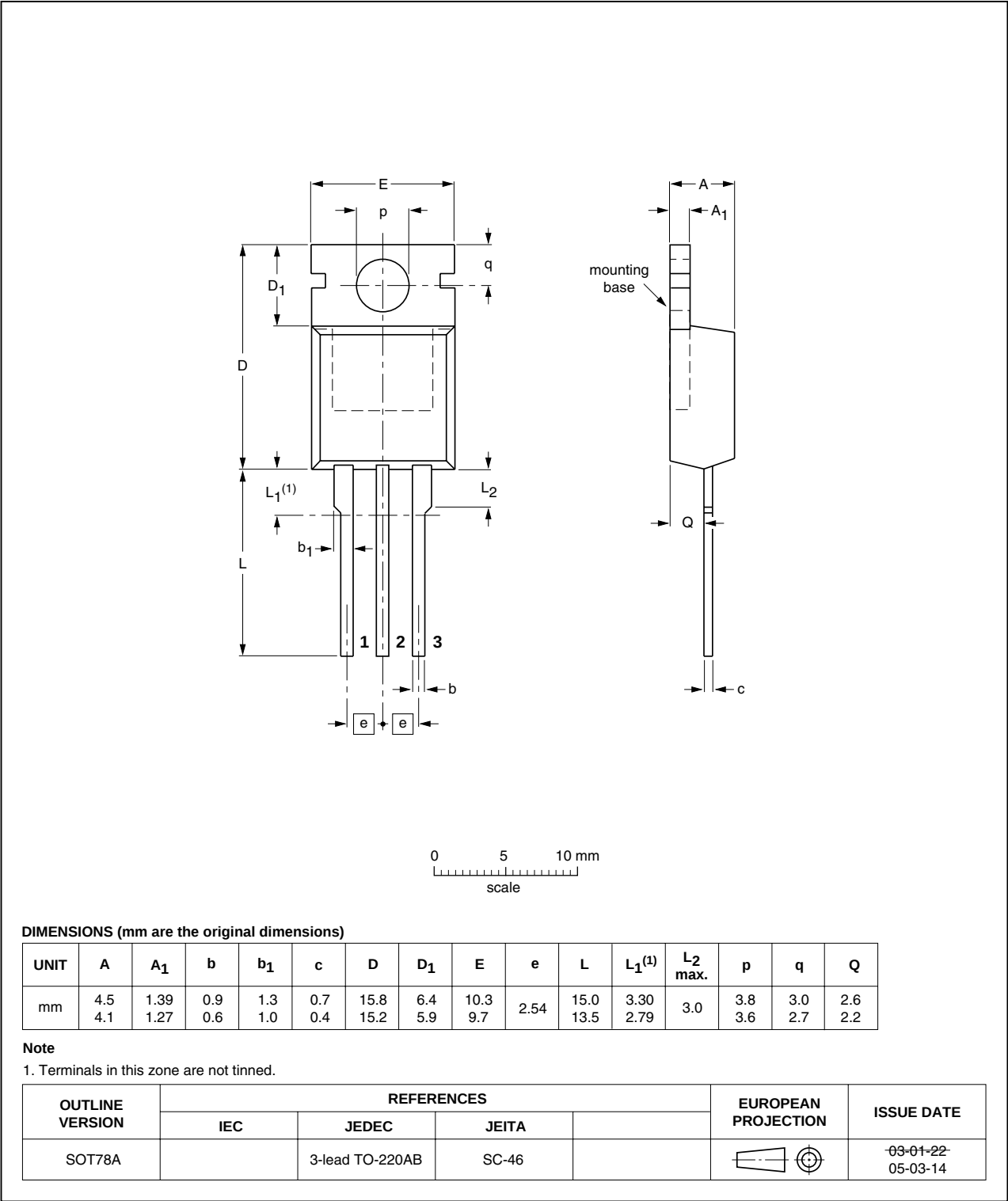


Fig 18. Package outline SOT78A (TO-220AB)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9515-100A v.3	20110419	Product data sheet	-	BUK9515_9615-100A_2
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Type number BUK9515-100A separated from data sheet BUK9515_9615-100A_2.			
BUK9515_9615-100A_2	19991101	Product specification	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1] [2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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11. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Limiting values	2
5	Thermal characteristics	4
6	Characteristics	5
7	Package outline	9
8	Revision history	10
9	Legal information	11
9.1	Data sheet status	11
9.2	Definitions	11
9.3	Disclaimers	11
9.4	Trademarks	12
10	Contact information	12

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